



*flow*PIM E1

1200 V / 10 A

Features

- Trench Fieldstop IGBT4 technology
- Standard industrial housing
- Optimized $R_{th(j-s)}$ with Phase-change Material
- Built-in NTC

Target applications

- Industrial Drives

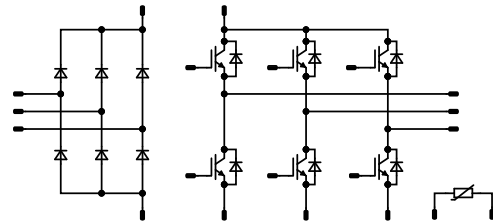
Types

- 10-EZ12PNA010SC-L927C08T

flow E1 12 mm housing



Schematic





Vincotech

10-EZ12PNA010SC-L927C08T
datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	18	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	30	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	59	W
Gate-emitter voltage	V_{GES}		± 20	V
Short circuit ratings	t_{SC}	$V_{GE} = 15\text{ V}$, $V_{CC} = 800\text{ V}$ $T_j = 150\text{ °C}$	10	μs
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$
Inverter Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	20	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	50	W
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$
Rectifier Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	47	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, $t_p = 10\text{ ms}$ $T_j = 150\text{ °C}$	270	A
Surge current capability	I^2t		370	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	61	W
Maximum junction temperature	T_{jmax}		150	$^{\circ}\text{C}$



Vincotech

10-EZ12PNA010SC-L927C08T
datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
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Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+($T_{jmax} - 25$)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Isolation voltage	V_{isol}	AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			>12,7	mm
Clearance			>12,7	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production



Vincotech

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Inverter Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$				0,00035	25	5,3	5,8	6,3	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	15			10	25 125 150	1,58	1,78 2,06 2,1	2,07 ⁽¹⁾	V
Collector-emitter cut-off current	I_{CES}	0	1200			25			1,2	μA
Gate-emitter leakage current	I_{GES}	20	0			25			120	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	$f = 1 \text{ Mhz}$	0	25		25		625		pF
Reverse transfer capacitance	C_{res}							40		pF

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK}$ (PSX)						1,6		K/W
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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 32 \Omega$ $R_{goff} = 32 \Omega$	±15	600	10	25		62,2		ns			
						125		61,4					
						150		60,2					
Rise time	t_r									25		24	ns
										125		24	
										150		25,6	
Turn-off delay time	$t_{d(off)}$									25		186	ns
						125		243,2					
						150		259					
Fall time	t_f					25		96,61	ns				
						125		155,41					
						150		162,07					
Turn-on energy (per pulse)	E_{on}	$Q_{rFWD} = 0,908 \mu\text{C}$ $Q_{tFWD} = 1,69 \mu\text{C}$ $Q_{rFWD} = 1,92 \mu\text{C}$				25		0,591	mWs				
						125		0,848					
						150		0,931					
Turn-off energy (per pulse)	E_{off}					25		0,637	mWs				
						125		0,979					
						150		1,11					



Vincotech

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datasheet

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		
Inverter Diode										
Static										
Forward voltage	V_F				10	25 125 150	1,35	1,79 1,77 1,73	2,05 ⁽¹⁾	V
Reverse leakage current	I_R	$V_r = 1200$ V				25			2,7	μA
Thermal										
Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,91		K/W
Dynamic										
Peak recovery current	I_{RRM}					25 125 150		8,15 10,41 10,68		A
Reverse recovery time	t_{rr}					25 125 150		261,02 402,82 435,67		ns
Recovered charge	Q_r	$di/dt=425$ A/μs $di/dt=421$ A/μs $di/dt=405$ A/μs	±15	600	10	25 125 150		0,908 1,69 1,92		μC
Reverse recovered energy	E_{rec}					25 125 150		0,358 0,684 0,782		mWs
Peak rate of fall of recovery current	$(di_r/dt)_{max}$					25 125 150		64,32 62,24 55,11		A/μs



Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Rectifier Diode

Static

Forward voltage	V_F				28	25 125		1,15 1,11	1,5 ⁽¹⁾	V
Reverse leakage current	I_R	$V_i = 1600$ V				25 150			100 1000	μA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,15		K/W
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Thermistor

Static

Rated resistance	R					25		5		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	$R_{100} = 493$ Ω				100	-5		5	%
Power dissipation	P							245		mW
Power dissipation constant	d					25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. ±2 %						3375		K
B-value	$B_{(25/100)}$	Tol. ±2 %						3437		K
Vincotech Thermistor Reference									K	

⁽¹⁾ Value at chip level

⁽²⁾ Only valid with pre-applied Vincotech thermal interface material.



Inverter Switch Characteristics

figure 1. IGBT

Typical output characteristics
 $I_C = f(V_{CE})$

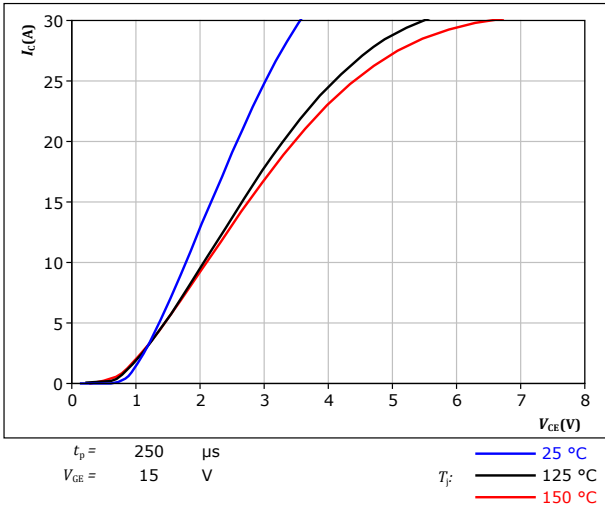


figure 2. IGBT

Typical output characteristics
 $I_C = f(V_{CE})$

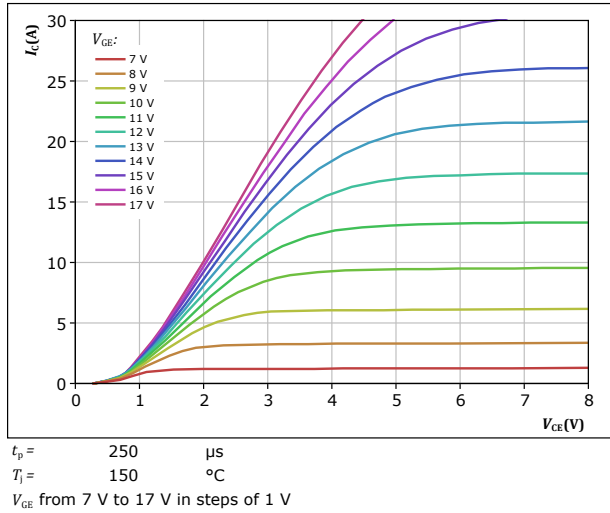


figure 3. IGBT

Typical transfer characteristics
 $I_C = f(V_{GE})$

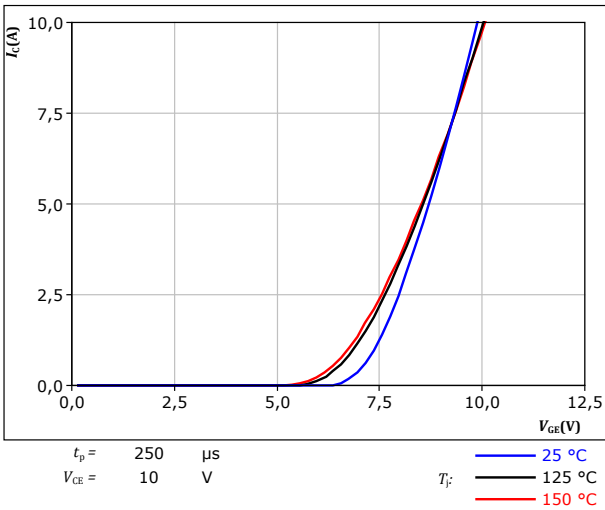
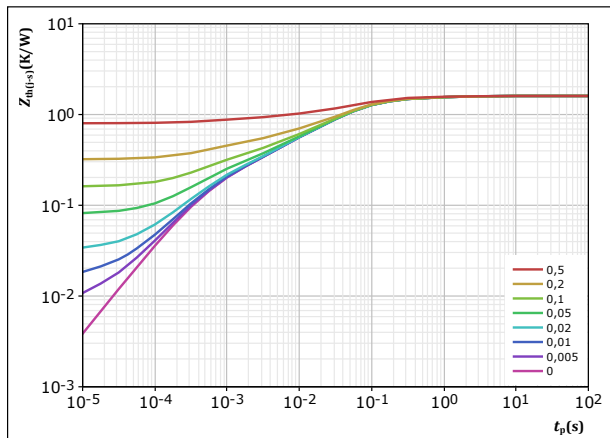


figure 4. IGBT

Transient thermal impedance as a function of pulse width
 $Z_{th(j-s)} = f(t_p)$



$D = t_p / T$
 $R_{th(j-s)} = 1,602 \text{ K/W}$

IGBT thermal model values

R (K/W)	τ (s)
7,97E-02	1,70E+00
1,68E-01	2,57E-01
8,12E-01	5,68E-02
2,44E-01	1,27E-02
1,49E-01	3,21E-03
1,48E-01	4,82E-04

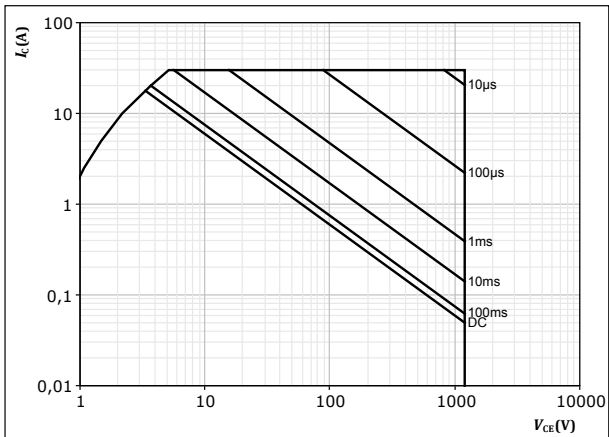


Inverter Switch Characteristics

figure 5. IGBT

Safe operating area

$$I_C = f(V_{CE})$$



- $D =$ single pulse
- $T_s = 80$ °C
- $V_{GE} = 15$ V
- $T_j = T_{jmax}$



Inverter Diode Characteristics

figure 6. FWD

Typical forward characteristics

$$I_F = f(V_F)$$

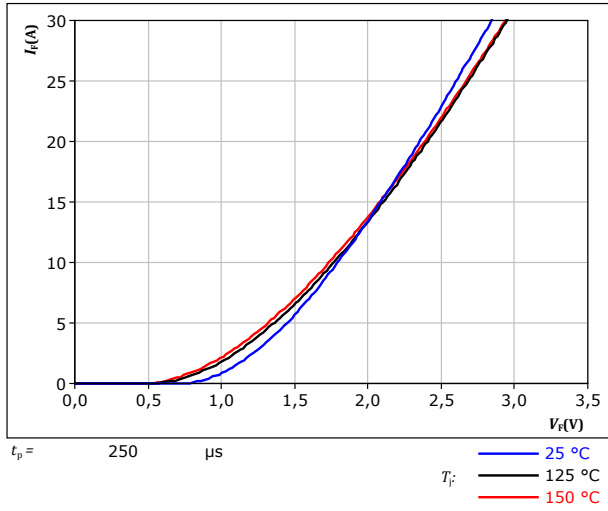
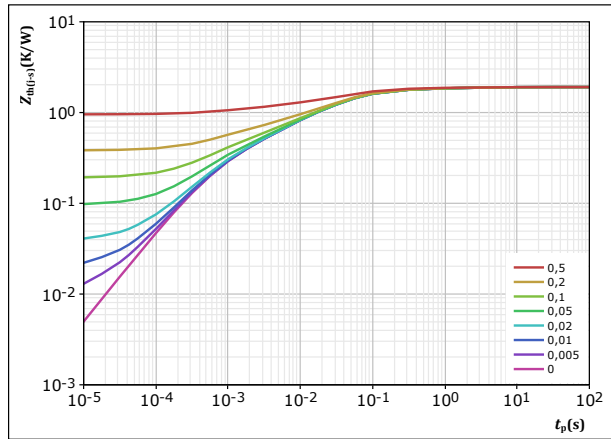


figure 7. FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = \frac{t_p}{T}$
 $R_{th(j-s)} = 1,909 \text{ K/W}$
 FWD thermal model values

R (K/W)	τ (s)
6,90E-02	3,61E+00
1,74E-01	3,07E-01
8,07E-01	4,87E-02
3,70E-01	1,36E-02
2,79E-01	3,22E-03
2,10E-01	5,68E-04



Rectifier Diode Characteristics

figure 8. Rectifier

Typical forward characteristics

$$I_F = f(V_F)$$

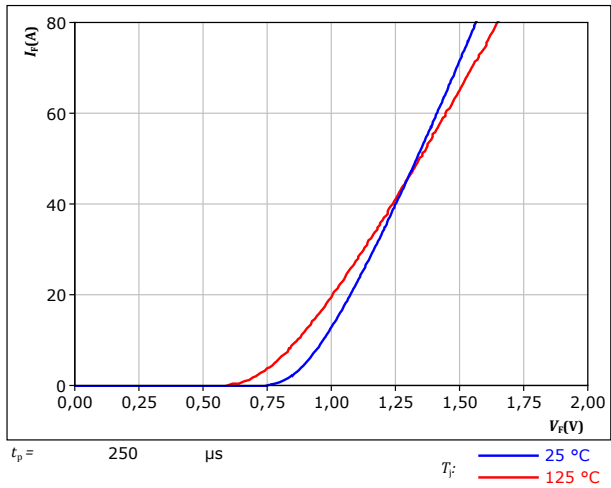
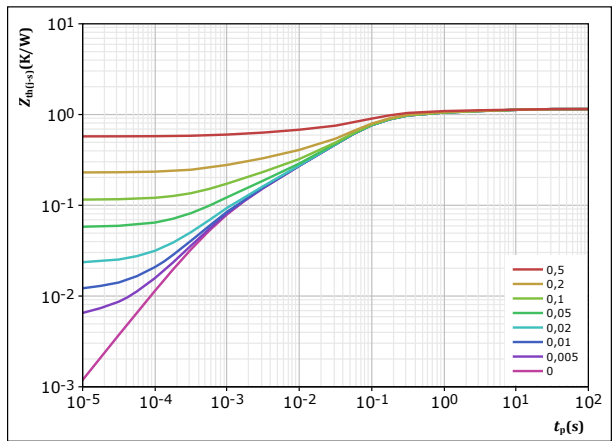


figure 9. Rectifier

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,149 \text{ K/W}$

Rectifier thermal model values

R (K/W)	τ (s)
8,29E-02	7,59E+00
1,02E-01	6,72E-01
4,20E-01	1,19E-01
3,78E-01	4,22E-02
1,08E-01	4,04E-03
5,78E-02	7,21E-04

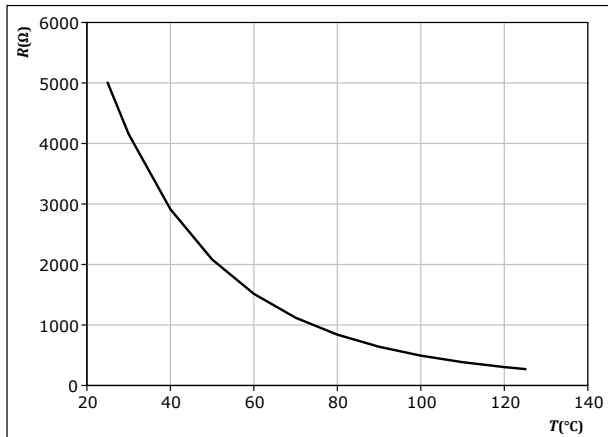


Thermistor Characteristics

figure 10. Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$

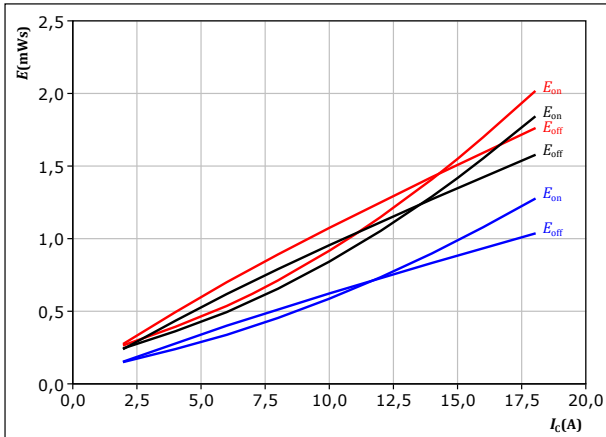




Inverter Switching Characteristics

figure 11. IGBT

Typical switching energy losses as a function of collector current
 $E = f(I_c)$

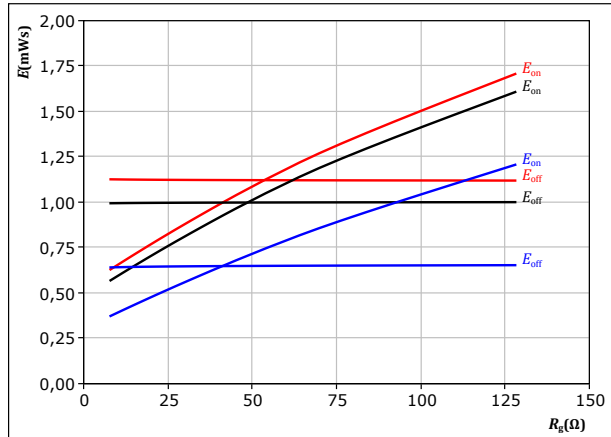


With an inductive load at

$V_{CE} = 600 \text{ V}$	$T_j: 25 \text{ }^\circ\text{C}$
$V_{GE} = \pm 15 \text{ V}$	$125 \text{ }^\circ\text{C}$
$R_{g(on)} = 32 \text{ } \Omega$	$150 \text{ }^\circ\text{C}$
$R_{g(off)} = 32 \text{ } \Omega$	

figure 12. IGBT

Typical switching energy losses as a function of gate resistor
 $E = f(R_g)$

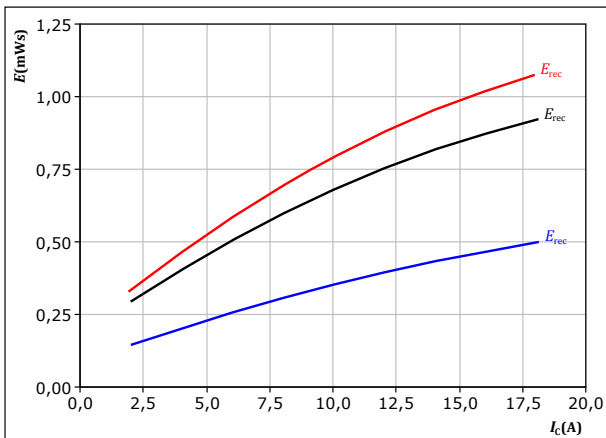


With an inductive load at

$V_{CE} = 600 \text{ V}$	$T_j: 25 \text{ }^\circ\text{C}$
$V_{GE} = \pm 15 \text{ V}$	$125 \text{ }^\circ\text{C}$
$I_c = 10 \text{ A}$	$150 \text{ }^\circ\text{C}$

figure 13. FWD

Typical reverse recovered energy loss as a function of collector current
 $E_{rec} = f(I_c)$

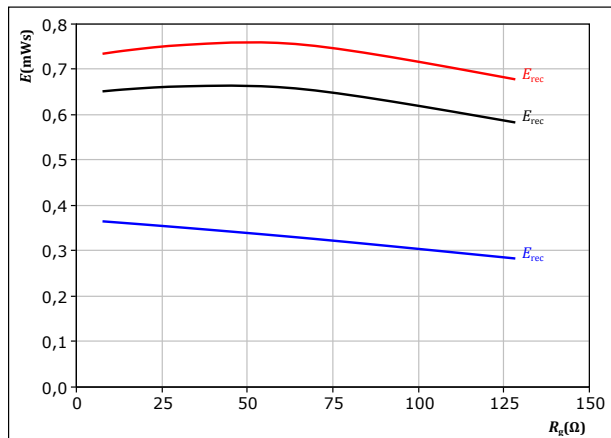


With an inductive load at

$V_{CE} = 600 \text{ V}$	$T_j: 25 \text{ }^\circ\text{C}$
$V_{GE} = \pm 15 \text{ V}$	$125 \text{ }^\circ\text{C}$
$R_{g(on)} = 32 \text{ } \Omega$	$150 \text{ }^\circ\text{C}$

figure 14. FWD

Typical reverse recovered energy loss as a function of gate resistor
 $E_{rec} = f(R_g)$



With an inductive load at

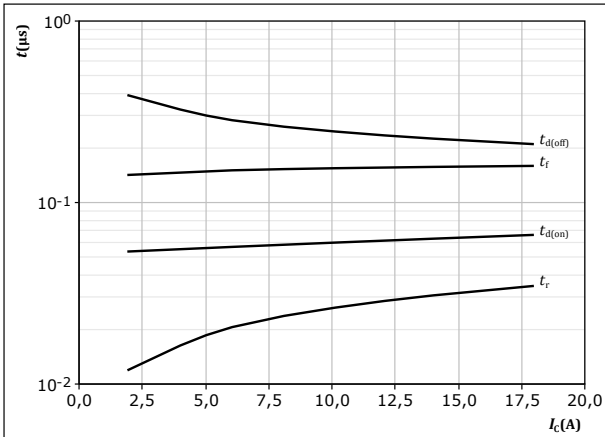
$V_{CE} = 600 \text{ V}$	$T_j: 25 \text{ }^\circ\text{C}$
$V_{GE} = \pm 15 \text{ V}$	$125 \text{ }^\circ\text{C}$
$I_c = 10 \text{ A}$	$150 \text{ }^\circ\text{C}$



Inverter Switching Characteristics

figure 15. IGBT

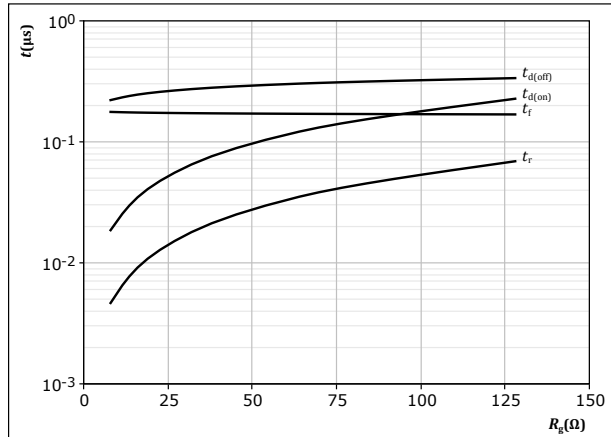
Typical switching times as a function of collector current
 $t = f(I_c)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 32 \text{ } \Omega$
 $R_{goff} = 32 \text{ } \Omega$

figure 16. IGBT

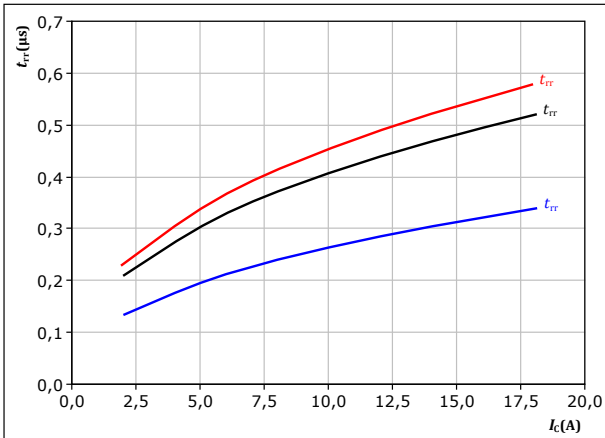
Typical switching times as a function of gate resistor
 $t = f(R_g)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 10 \text{ A}$

figure 17. FWD

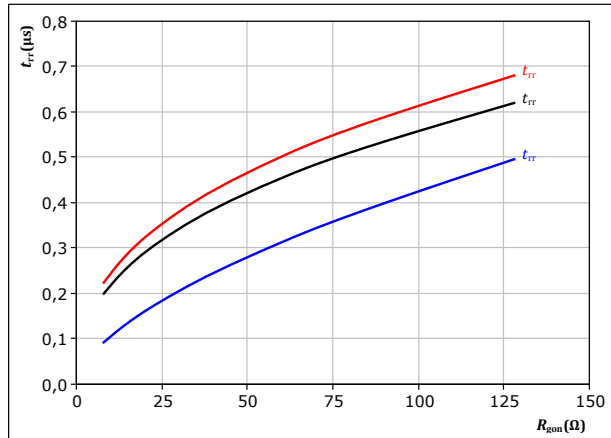
Typical reverse recovery time as a function of collector current
 $t_{rr} = f(I_c)$



With an inductive load at
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 32 \text{ } \Omega$
 $T_j:$ — 25 °C
 — 125 °C
 — 150 °C

figure 18. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor
 $t_{rr} = f(R_{gon})$



With an inductive load at
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 10 \text{ A}$
 $T_j:$ — 25 °C
 — 125 °C
 — 150 °C

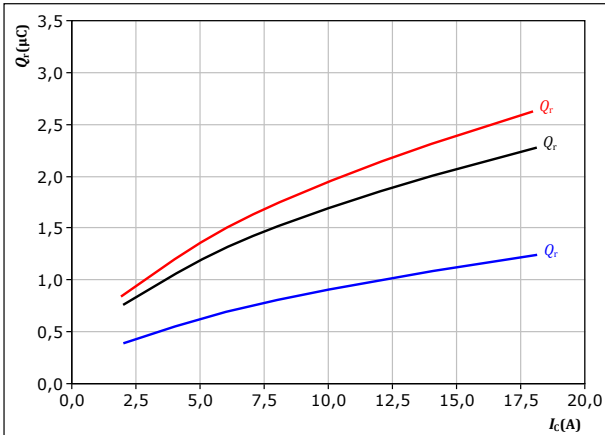


Inverter Switching Characteristics

figure 19. FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_c)$$



With an inductive load at

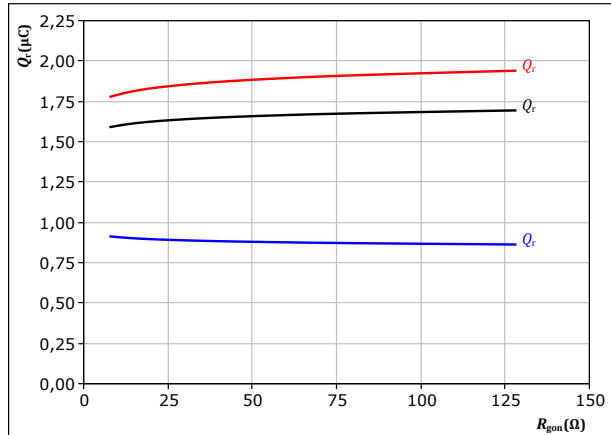
$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 32$ Ω

T_j : — 25 °C
— 125 °C
— 150 °C

figure 20. FWD

Typical recovered charge as a function of turn on gate resistor

$$Q_r = f(R_{gon})$$



With an inductive load at

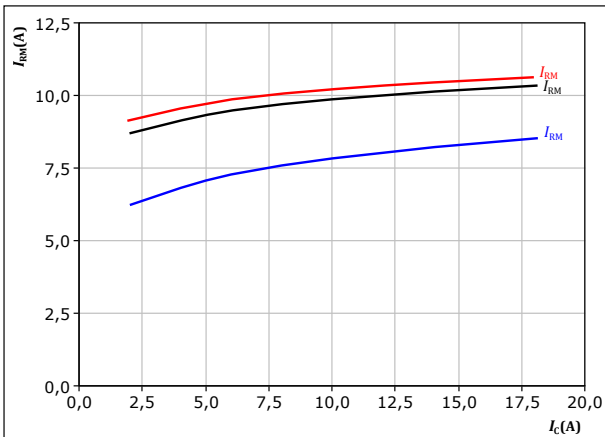
$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 10$ A

T_j : — 25 °C
— 125 °C
— 150 °C

figure 21. FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_c)$$



With an inductive load at

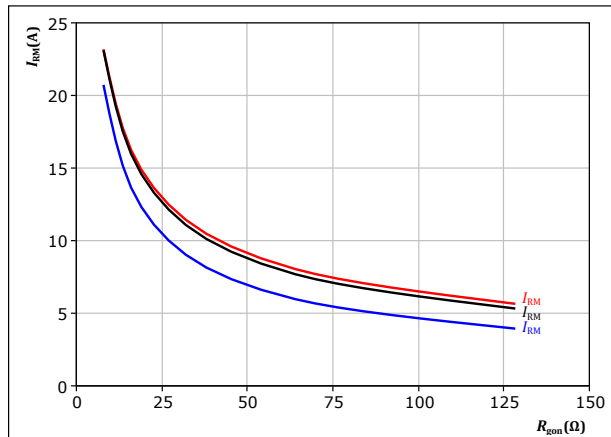
$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 32$ Ω

T_j : — 25 °C
— 125 °C
— 150 °C

figure 22. FWD

Typical peak reverse recovery current as a function of turn on gate resistor

$$I_{RM} = f(R_{gon})$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 10$ A

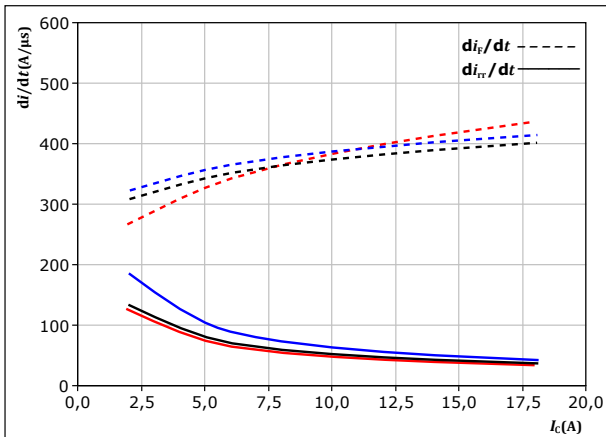
T_j : — 25 °C
— 125 °C
— 150 °C



Inverter Switching Characteristics

figure 23. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_f/dt, di_{rr}/dt = f(I_C)$

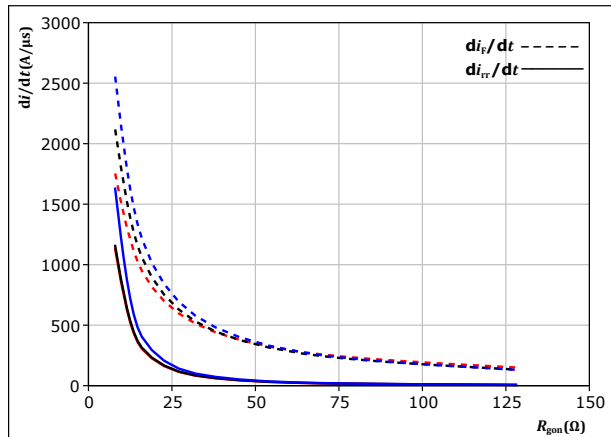


With an inductive load at

$V_{CE} =$	600	V	$T_j =$	25 °C
$V_{GE} =$	±15	V		125 °C
$R_{gon} =$	32	Ω		150 °C

figure 24. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_{rr}/dt = f(R_{gon})$

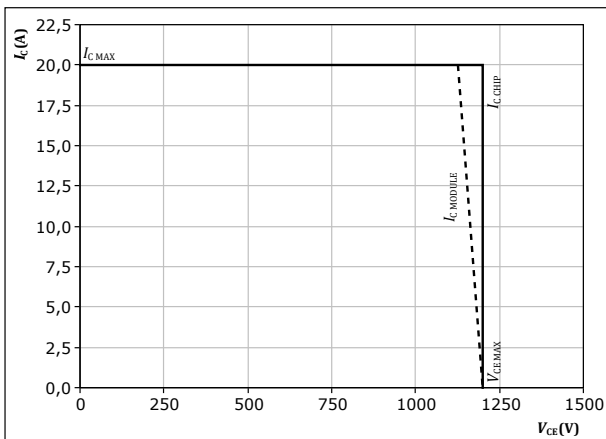


With an inductive load at

$V_{CE} =$	600	V	$T_j =$	25 °C
$V_{GE} =$	±15	V		125 °C
$I_C =$	10	A		150 °C

figure 25. IGBT

Reverse bias safe operating area
 $I_C = f(V_{CE})$



At

$T_j =$	150	°C
$R_{gon} =$	32	Ω
$R_{goff} =$	32	Ω



Inverter Switching Definitions

figure 26. IGBT
Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})

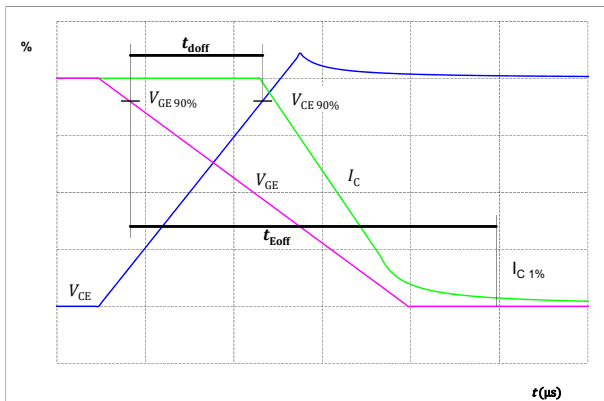


figure 27. IGBT
Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})

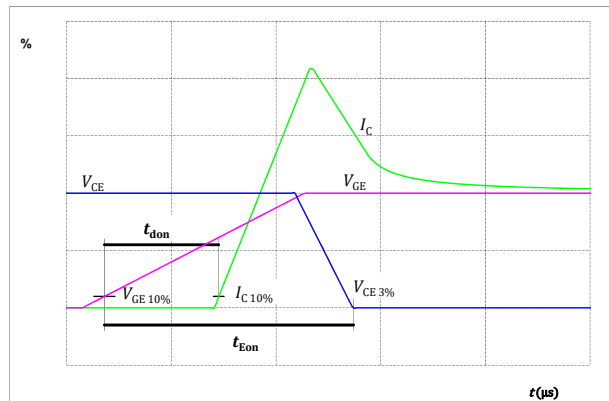


figure 28. IGBT
Turn-off Switching Waveforms & definition of t_f

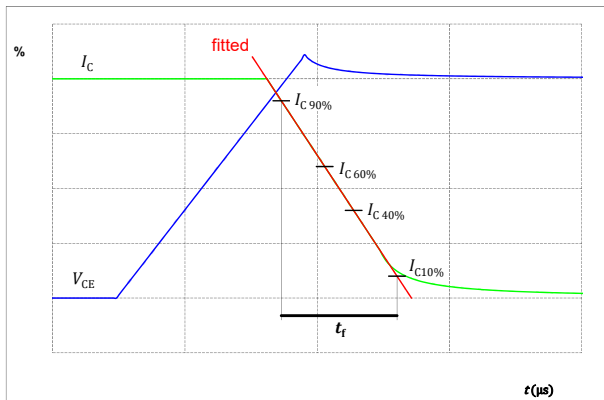
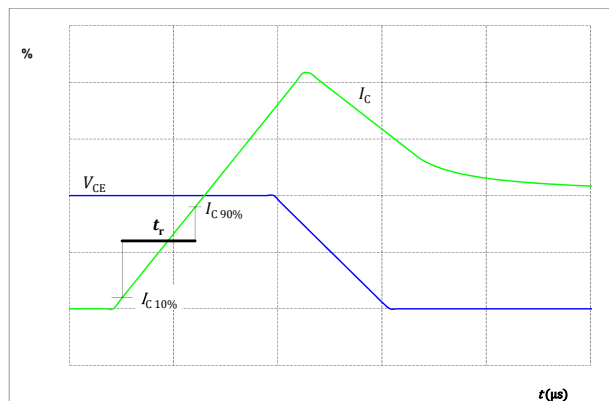


figure 29. IGBT
Turn-on Switching Waveforms & definition of t_r





Inverter Switching Definitions

figure 30. FWD

Turn-off Switching Waveforms & definition of t_{rr}

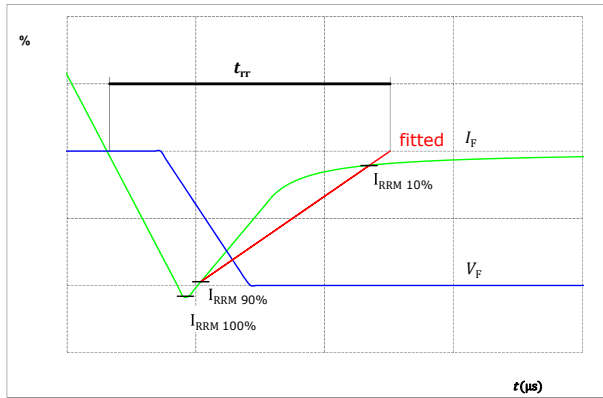
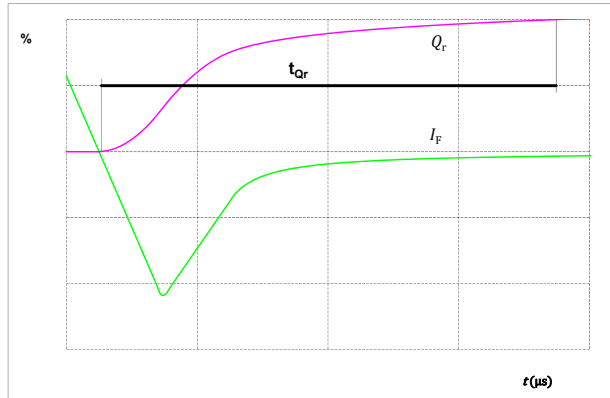


figure 31. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)




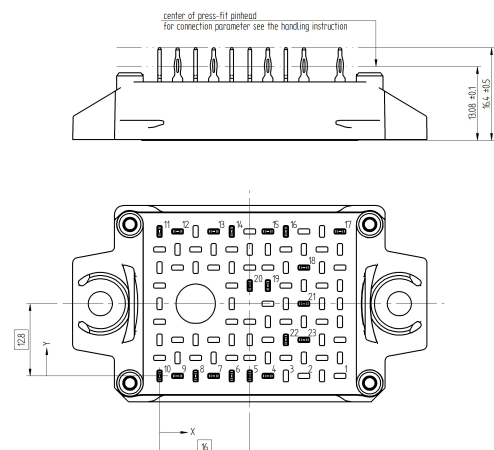


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10-EZ12PNA010SC-L927C08T
datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	10-EZ12PNA010SC-L927C08T
With thermal paste	10-EZ12PNA010SC-L927C08T-/3/

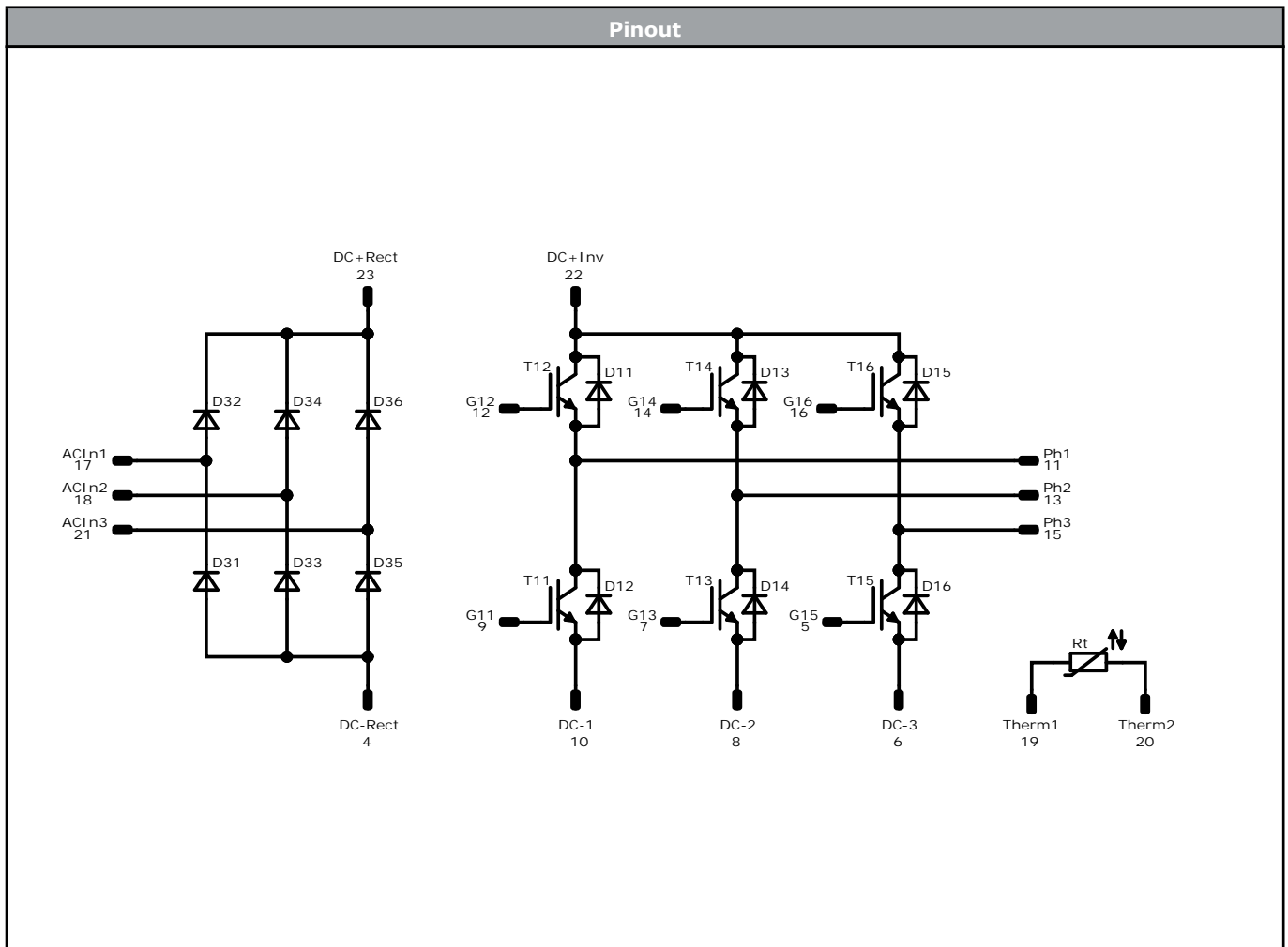
Marking						
	Text	Name NN-NNNNNNNNNNNNNN- TTTTTVV	Date code WWYY	UL & VIN UL VIN	Lot LLLLL	Serial SSSS
	Datamatrix	Type&Ver TTTTTTTV	Lot number LLLLL	Serial SSSS	Date code WWYY	

Pin table [mm]				Outline
Pin	X	Y	Function	
1			not assembled	
2			not assembled	
3			not assembled	
4	19,2	0	DC-Rect	
5	16	0	G15	
6	12,8	0	DC-3	
7	9,6	0	G13	
8	6,4	0	DC-2	
9	3,2	0	G11	
10	0	0	DC-1	
11	0	25,6	Ph1	
12	3,2	25,6	G12	
13	9,6	25,6	Ph2	
14	12,8	25,6	G14	
15	19,2	25,6	Ph3	
16	22,4	25,6	G16	
17	32	25,6	ACIn1	
18	25,6	19,2	ACIn2	
19	19,2	16	Therm1	
20	16	16	Therm2	
21	25,6	12,8	ACIn3	
22	22,4	6,4	DC+Inv	
23	25,6	6,4	DC+Rect	

Tolerance of pinpositions: ±0.4mm at the end of pins
Dimension of coordinate axis is only offset without tolerance



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Identification					
ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	10 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	10 A	Inverter Diode	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	28 A	Rectifier Diode	
Rt	NTC			Thermistor	




Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow</i> E1 packages see vincotech.com website.

Package data
Package data for <i>flow</i> E1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website. 

Document No.:	Date:	Modification:	Pages
10-EZ12PNA010SC-L927C08T-D3-14	31 Mar. 2021	New datasheet format Update characteristics of rectifier diode, leakage current max value from 50 -> 100 uA	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.